

# FQP19N20L

## 200V LOGIC N-Channel MOSFET

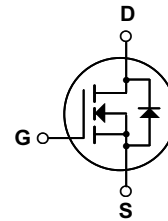
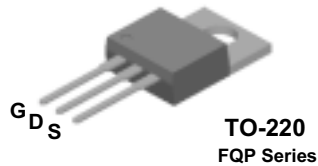
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply, motor control.

### Features

- 21A, 200V,  $R_{DS(on)} = 0.14\Omega @ V_{GS} = 10\text{ V}$
- Low gate charge ( typical 27 nC)
- Low  $C_{rss}$  ( typical 30 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- Low level gate drive requirement allowing direct operation from logic drivers



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP19N20L	Units
$V_{DSS}$	Drain-Source Voltage	200	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	21	A
		13.3	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	84	A
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	250	mJ
$I_{AR}$	Avalanche Current (Note 1)	21	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	14	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	140	W
		1.12	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.89	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics**T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	200	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	--	0.16	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	--	--	1	μA
		V <sub>DS</sub> = 160 V, T <sub>C</sub> = 125°C	--	--	10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V	--	--	-100	nA

**On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0	--	2.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10.5 A	--	0.11	0.14	Ω
		V <sub>GS</sub> = 5 V, I <sub>D</sub> = 10.5 A (Note 4)	--	0.12	0.15	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 10.5 A	--	18.5	--	S

**Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	--	1700	2200	pF
C <sub>oss</sub>	Output Capacitance		--	220	290	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	30	40	pF

**Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 21 A, R <sub>G</sub> = 25 Ω (Note 4, 5)	--	35	80	ns
t <sub>r</sub>	Turn-On Rise Time		--	300	610	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	130	270	ns
t <sub>f</sub>	Turn-Off Fall Time		--	180	370	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 160 V, I <sub>D</sub> = 21 A, V <sub>GS</sub> = 5 V (Note 4, 5)	--	27	35	nC
Q <sub>gs</sub>	Gate-Source Charge		--	5.8	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	11.2	--	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current	--	--	21	A	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current	--	--	84	A	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 21 A	--	--	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 21 A, (Note 4) dI <sub>F</sub> / dt = 100 A/μs	--	140	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	0.66	--	μC

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 0.85mH, I<sub>AS</sub> = 21A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 21A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

## Typical Characteristics

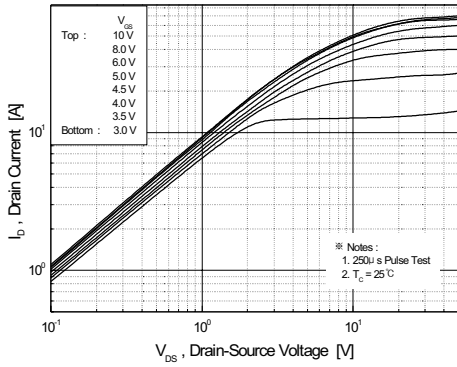


Figure 1. On-Region Characteristics

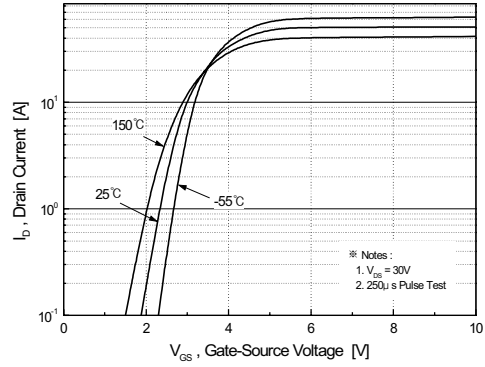


Figure 2. Transfer Characteristics

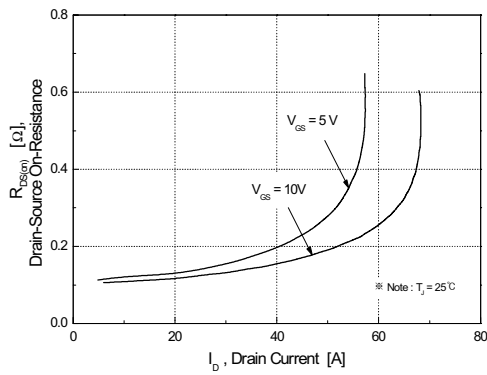


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

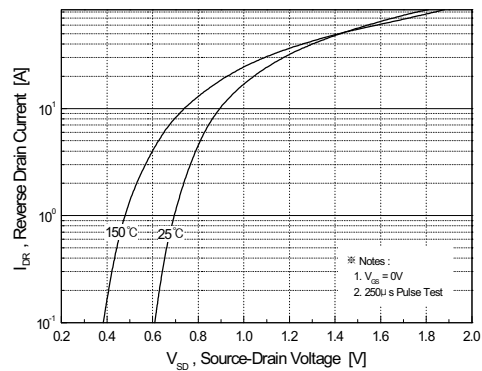


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

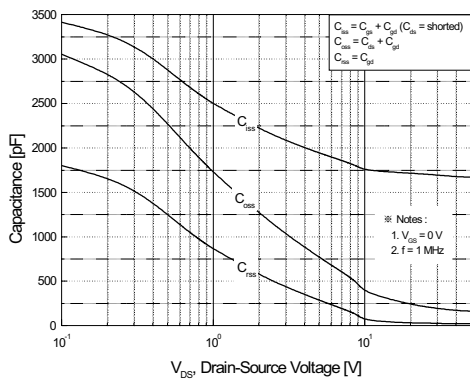


Figure 5. Capacitance Characteristics

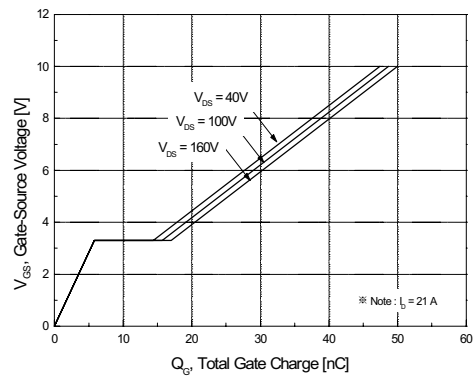
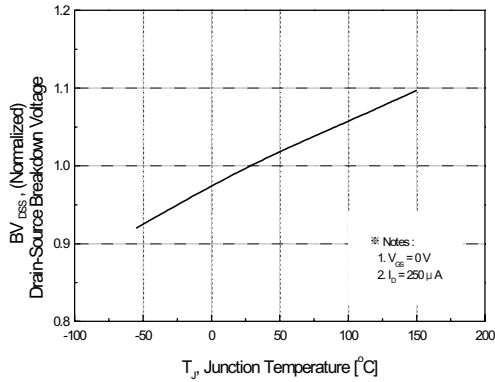
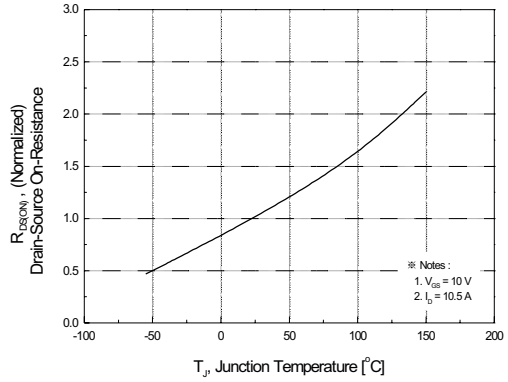


Figure 6. Gate Charge Characteristics

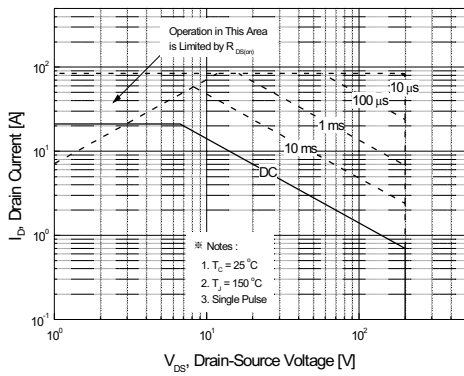
**Typical Characteristics** (Continued)



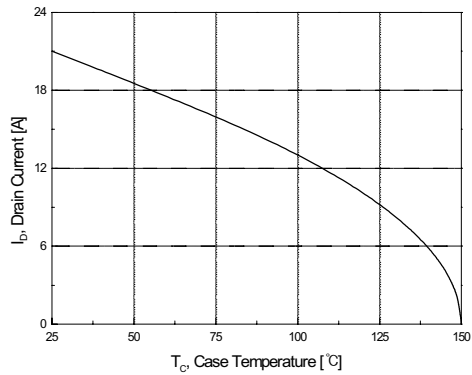
**Figure 7. Breakdown Voltage Variation vs. Temperature**



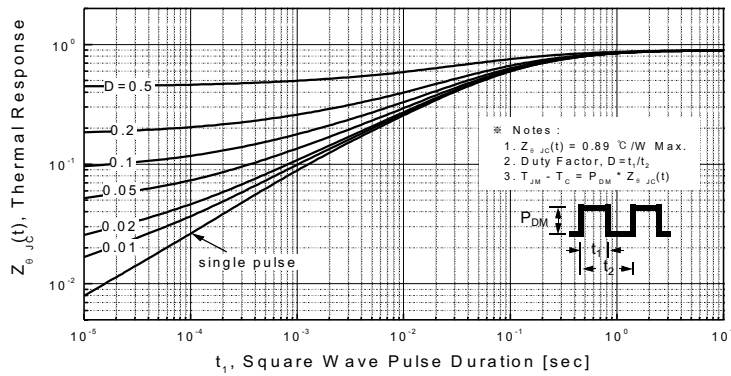
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

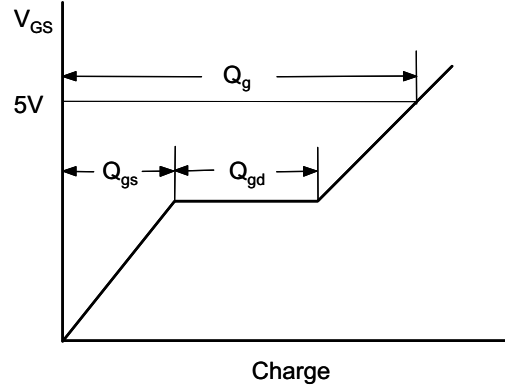
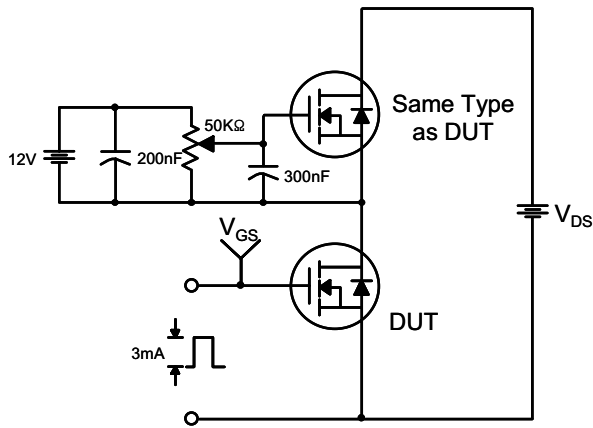


**Figure 10. Maximum Drain Current vs. Case Temperature**

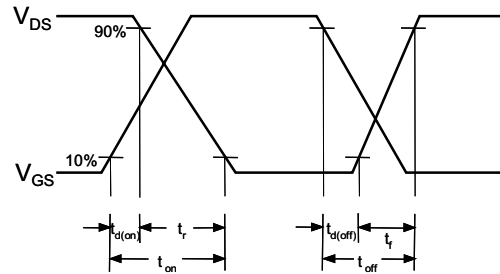
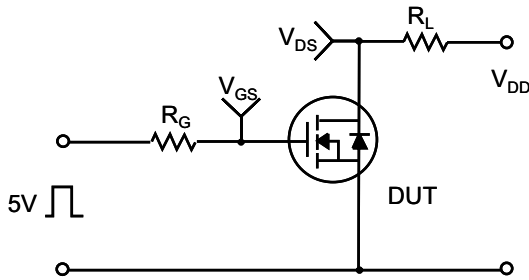


**Figure 11. Transient Thermal Response Curve**

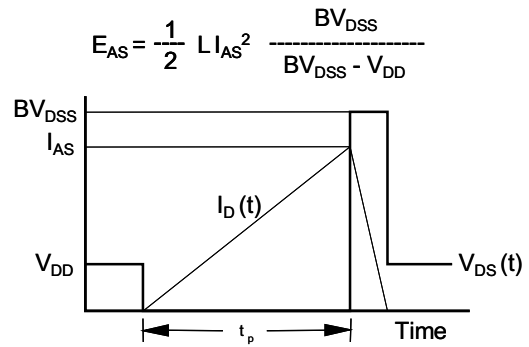
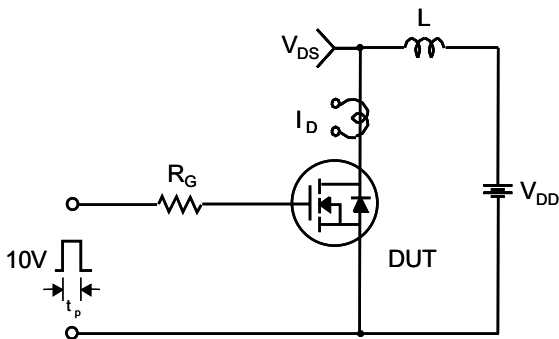
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

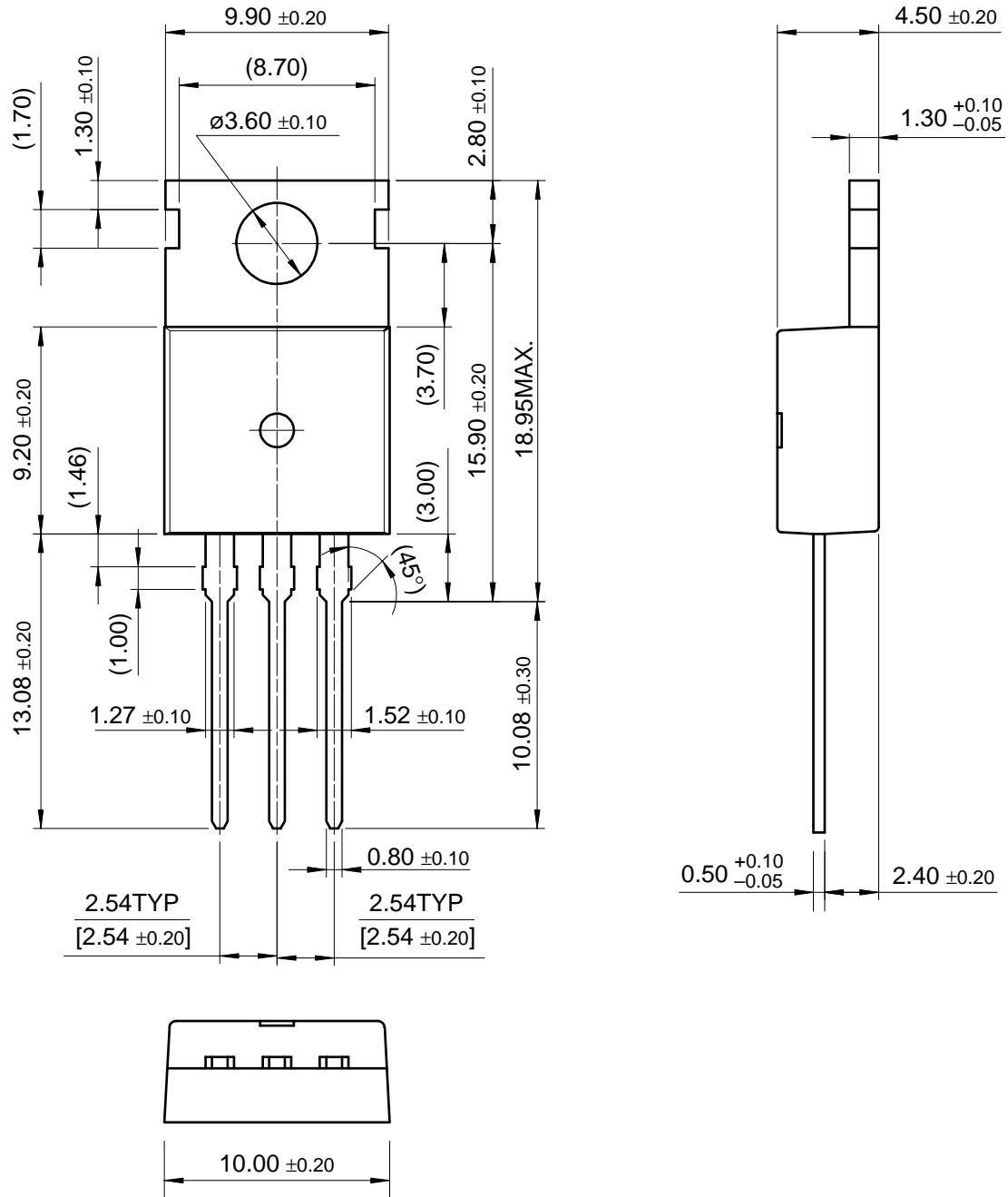


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220



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